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TRANSMITTAL LETTER
(General - Patent Pending)

Docket No.
51889/3

Application Of: Douglas R. Hackler, Sr. et al.

Serial No.
10/719,119

Filing Date
November 21, 2003

Examiner
Not yet assigned

Group Art Unit
2814

Title: **DOUBLE-GATED TRANSISTOR CIRCUIT**

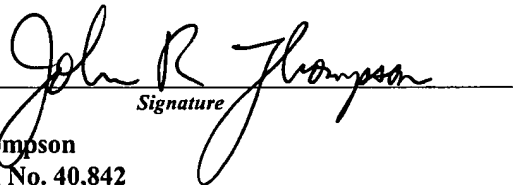
TO THE COMMISSIONER FOR PATENTS:

Transmitted herewith is:

Information Disclosure Statement
PTO-1449 with copies of cited articles
Postcard

in the above identified application.

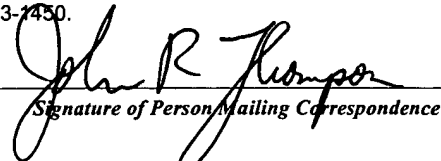
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Signature

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Dated: March 18, 2004

I certify that this document and fee is being deposited on March 18, 2004 with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Douglas R. Hackler, Sr. et al.

Confirmation No. 1799

Application No. 10/719,119

Filed: November 21, 2003

For: **DOUBLE-GATED TRANSISTOR
CIRCUIT**

Group Art Unit: 2814

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INFORMATION DISCLOSURE STATEMENT

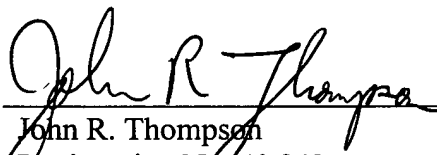
TO THE COMMISSIONER FOR PATENTS:

1. Pursuant to the duty of disclosure, documents listed on the accompanying Form PTO-1449 (or equivalent) are presented for the Examiner's consideration.
 - ☒ Copies of listed documents are enclosed. (37 CFR § 1.98(a))
 - ☒ Copies of listed U.S. patent documents are omitted because this application was filed after June 30, 2003 and is, thus, subject to image file wrapper processing. Copies of listed foreign patent documents and non-patent literature are enclosed.
 - ☐ Copies of the documents listed on sheet(s) _____ of Form PTO-1449 (or equivalent) are omitted because (1) they are already of record in U.S. Patent Application No. _____, filed _____, on which this application relies for an earlier filing date under 35 U.S.C. § 120; and (2) any information disclosure statement filed in the prosecution of Application No. _____, complies with 37 CFR §§ 1.98(a) through (c). (37 C.F.R. § 1.98(d))
2. ☐ The Examiner's attention is directed to the enclosed copy of copending U.S. Patent Application No. _____, filed _____, for _____, which is cited in this application.
3. This information disclosure statement is being submitted (check box a., b., or c.):
 - a. ☒ Within three months of the filing date of a national application or entry of the national stage in an international application; or before the mailing of a first Office action on the merits; or before the mailing of a first Office action after the filing of a request for continued examination under 37 CFR 1.114. (No statement under 37 CFR 1.97(e) is required.); or

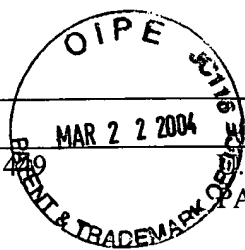


- b. ☐ After the period set forth in paragraph 3a, but before the mailing date of either a final action, a notice of allowance, or an action that otherwise closes prosecution in the application. (Check box i. or ii.)
- i. ☐ A \$180.00 information disclosure statement submission fee set forth in 37 CFR 1.17(p) is enclosed, or
- ii. ☐ A statement specified by 37 CFR 1.97(e) is set forth below; or
- c. ☐ After the mailing date of a final action or notice of allowance and on or before payment of the issue fee. A statement specified by 37 CFR 1.97(e) is set forth below. Enclosed is a \$180.00 information disclosure statement processing fee set forth in 37 CFR 1.17(p).
4. If a statement specified by 37 CFR 1.97(e) is required, the attorney or agent signing below hereby states that:
- ☐ each item of information contained in the information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement; or
- ☐ no item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the information disclosure statement.
5. ☐ A concise explanation of the relevance of each document not in the English language and/or selected documents in the English language is set forth below.

Respectfully submitted,

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	1	2002/0187610 A1	12/12/02	Furukawa et al.	438	283	06/12/01
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FORM PTO-1449
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	17	5,349,228	09/20/94	Neudeck et al.	257	365	12/07/93
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FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	PUBLICA- TION DATE	COUNTRY / PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	20							
	21							
	22							
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	26							
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OTHER DOCUMENTS (Including Author, Title, Date, Relevant Pages, Place of Publication , etc.)

	28	Harada et al., "2-GHz RF Front-End Circuits in CMOS/SIMOX Operating at an Extremely Low Voltage of 0.5 V," IEEE Journal of Solid-State Circuits, Vol. 35, No. 12, December 2000, pgs. 2000-2004.
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90	Yagishita et al., "High Performance Metal Gate MOSFETs Fabricated by CMP for 0.1 μ m Regime," Microelectronics Engineering Laboratory, Toshiba Corporation, 8, Shinsugita-cho, Isogo-ku, Yokohama 235-8522, Japan, pgs. 29.3.1-29.3.4.
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